

N-Channel Enhancement Mode Field Effect Transistor

2N7002W

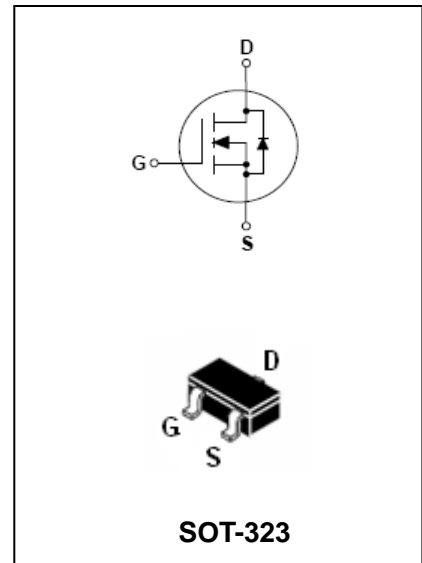
FEATURES

- High Density Cell Design For Low $R_{DS(ON)}$
- Voltage Controlled Small Signal Switch
- Rugged and Reliable
- High Saturation Current Capability
- MSL 1

HF

APPLICATIONS

- N-channel enhancement mode effect transistor
- Switching application



ORDERING INFORMATION

Type No.	Marking	Package Code
2N7002W	7002	SOT-323

MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{DSS}	Drain-Source voltage	60	V
V_{DGR}	Drain-Gate voltage($R_{GS} \leq 1\text{M}\Omega$)	60	V
V_{GSS}	Gate -Source voltage - continuous - Non Repetitive ($t_p < 50\mu\text{s}$)	± 20 ± 40	V
I_D	Maximum Drain current -continuous -Pulsed	115 800	mA
P_D	Power Dissipation	200	mW
$R_{\theta JA}$	Thermal resistance, Junction-to-Ambient	625	$^\circ\text{C}/\text{W}$
T_J, T_{stg}	Junction and Storage Temperature	-50 to +150	$^\circ\text{C}$

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ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	-	2	
Gate-body Leakage	I_{GSS}	Forward $V_{DS}=0V, V_{GS}=20V$	-	-	1	uA
		Reverse $V_{DS}=0V, V_{GS}=-20V$	-	-	-1	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$	-	-	1	μA
		$V_{DS}=60V, V_{GS}=0V, T_j=125^\circ C$	-	-	500	
Drain-Source on-voltage	$V_{DS(ON)}$	$V_{GS}=10V, I_D=500mA$	-	0.6	3.75	V
		$V_{GS}=5V, I_D=50mA$	-	0.09	1.5	
Forward transconductance	g_{FS}	$V_{DS}=10, I_D=200mA$	80	-	-	mS
Static drain-Source on-resistance	$R_{DS(ON)}$	$V_{GS}=5.0V, I_D=50mA$	-	3.2	7.5	Ω
		$V_{GS}=10V, I_D=500mA, T_j=100^\circ C$	-	4.4	13.5	
Drain-Source diode forward voltage	V_{SD}	$V_{GS}=0V, I_S=115mA$	-	0.88	1.5	V
Input capacitance	C_{ISS}	$V_{DS}=25V, V_{GS}=0V, f=1.0MHz$	-	20	50	pF
Output capacitance	C_{OSS}		-	11	25	
Reverse transfer capacitance	C_{RSS}		-	4	5	
Turn-On Delay Time	$t_{D(ON)}$	$V_{DD} = 30V, I_D= 0.2A,$ $R_L = 150\Omega, V_{GS}= 10V,$ $R_{GEN}= 25\Omega$	-	-	20	ns
Turn-Off Delay Time	$t_{D(OFF)}$		-	-	20	ns

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TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

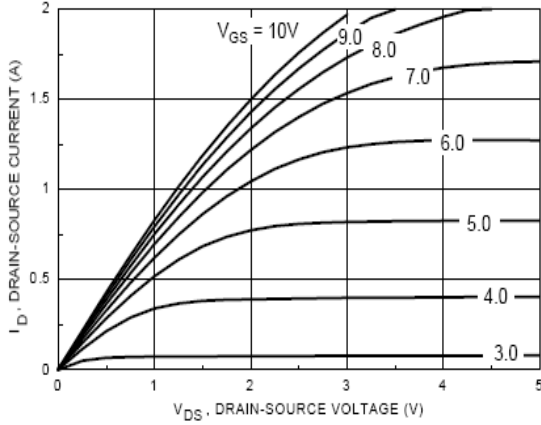


Figure 1. On-Region Characteristics

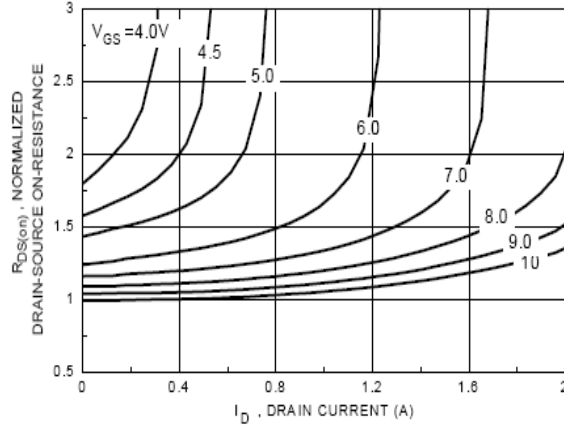


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current

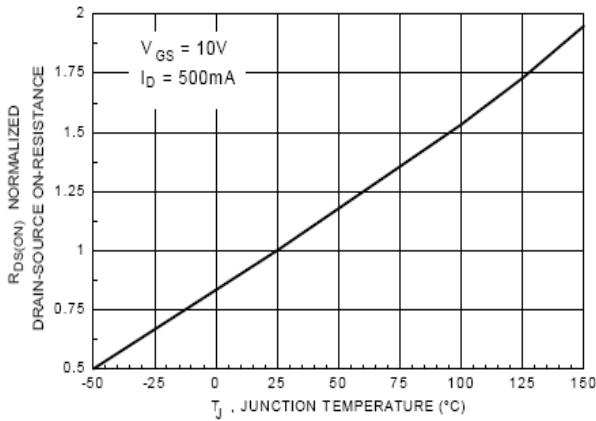


Figure 3. On-Resistance Variation with Temperature

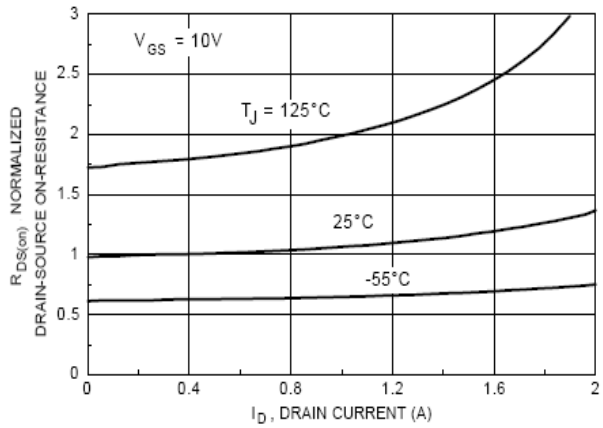


Figure 4. On-Resistance Variation with Drain Current and Temperature

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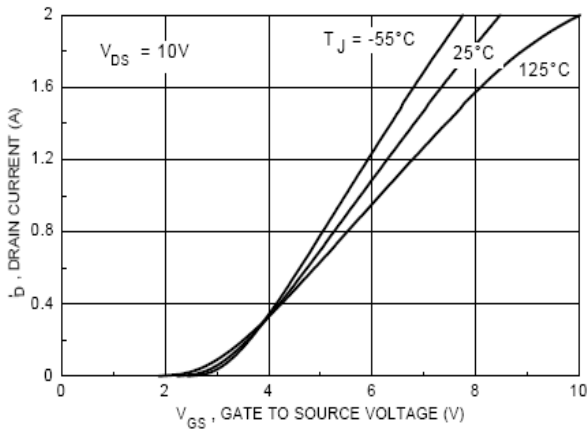


Figure 5. Transfer Characteristics

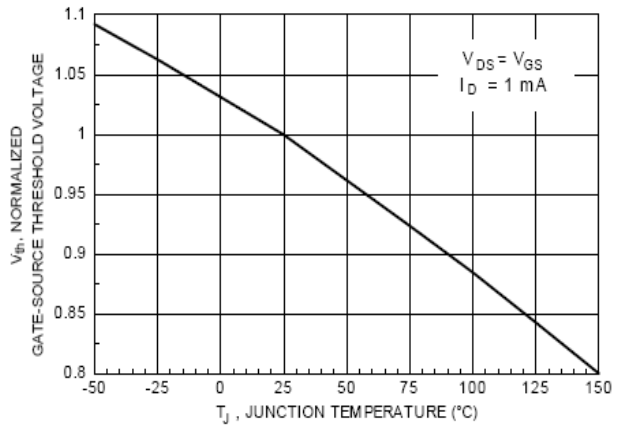


Figure 6. Gate Threshold Variation with Temperature

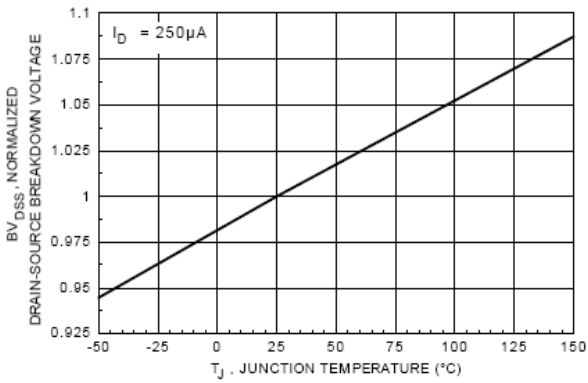


Figure 7. Breakdown Voltage Variation with Temperature

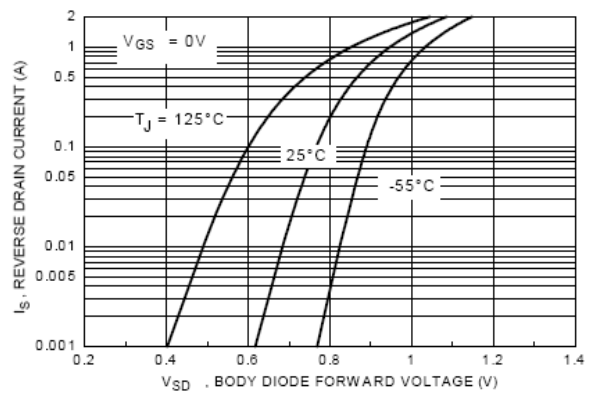


Figure 8. Body Diode Forward Voltage Variation with Temperature

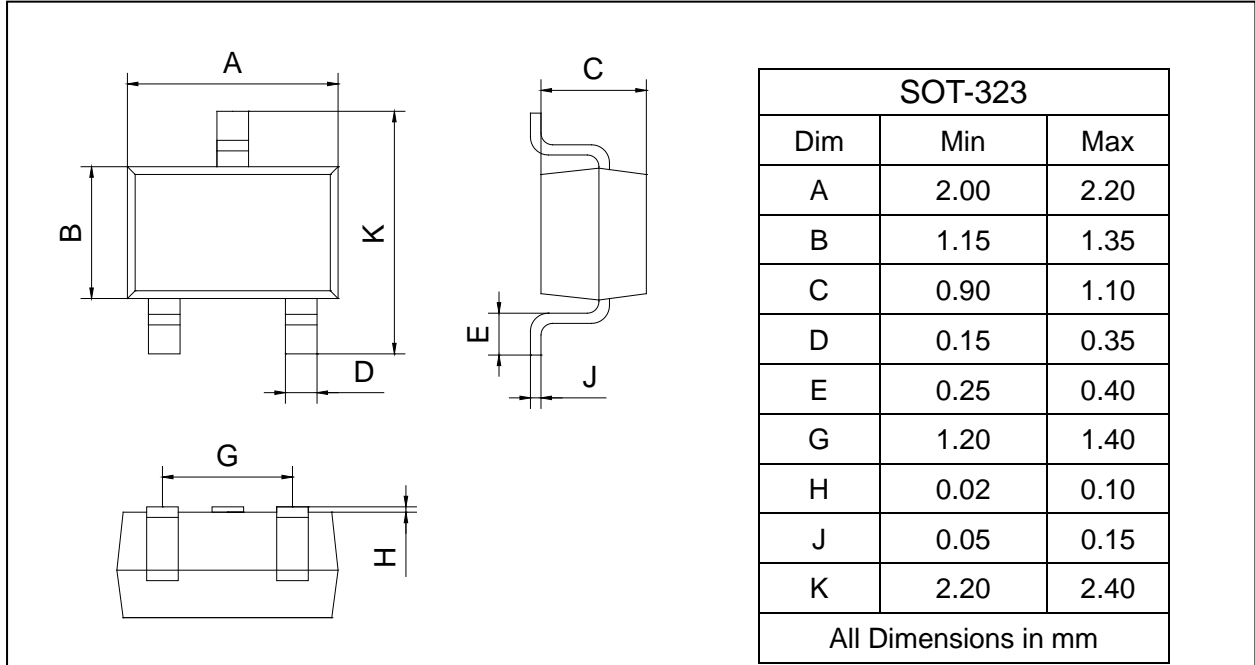
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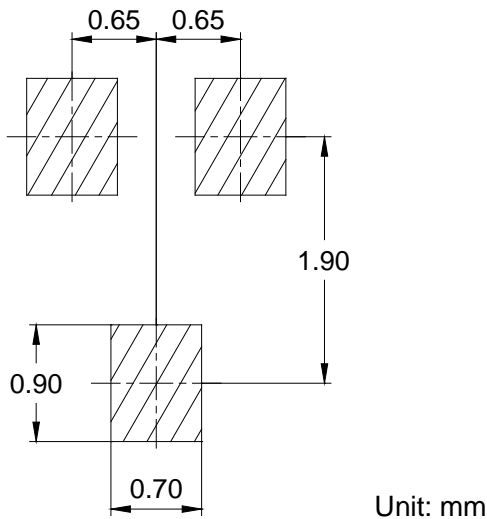
PACKAGE OUTLINE

Plastic surface mounted package

SOT-323



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
2N7002W	SOT-323	3000 pcs / Tape & Reel